Silicon N Channel Power MOS FET Power Switching

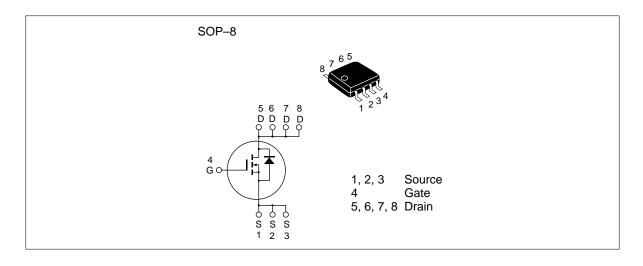
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ADE-208-565 A (Z) Target specification 2nd. Edition Sept. 1, 1997

Features

- Low on-resistance $R_{DS(on)} = 6.2 \text{ m}\Omega \text{ typ}$
- Capable of 4 V gate drive
- Low drive current
- High density mounting

Outline



Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	30	V
Gate to source voltage	$V_{\rm GSS}$	±20	V
Drain current	I _D	15	Α
Drain peak current	I _{D(pulse)} *1	120	A
Body to drain diode reverse drain current	I _{DR}	15	Α
Channel dissipation	Pch*2	2.5	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1 %

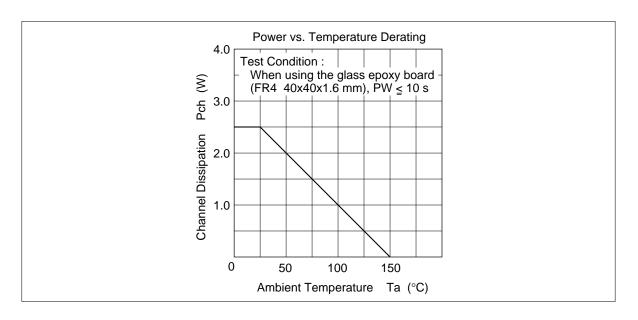
^{2.} When using the glass epoxy board (FR4 40 x 40 x 1.6 mm), PW \leq 10s

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	30	_	_	V	$I_{D} = 10 \text{mA}, V_{GS} = 0$
Gate to source leak current	I _{GSS}	_		±0.1	μΑ	$V_{GS} = \pm 20V, V_{DS} = 0$
Zero gate voltage drain current	I _{DSS}	_		1	μА	$V_{DS} = 30 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.0		2.5	V	$V_{DS} = 10V$, $I_D = 1mA$
Static drain to source on state	R _{DS(on)}	_	6.2	8.0	mΩ	$I_D = 8A, V_{GS} = 10V^{*1}$
resistance	$R_{\rm DS(on)}$		9.0	13.0	mΩ	$I_D = 8A, V_{GS} = 4V^{*1}$
Forward transfer admittance	y _{fs}	18	30	_	S	$I_D = 8A, V_{DS} = 10V^{*1}$
Input capacitance	Ciss	_	4400	_	pF	V _{DS} = 10V
Output capacitance	Coss		1100	_	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	_	500	_	pF	f = 1MHz
Total gate charge	Qg	_	90	_	nc	$V_{DD} = 10V$
Gate to source charge	Qgs		15	_	nc	$V_{GS} = 10V$
Gate to drain charge	Qgd	_	18	_	nc	I _D = 15A
Turn-on delay time	$t_{d(on)}$	_	110	_	ns	$V_{GS} = 4V$, $I_D = 8A$
Rise time	t _r		410	_	ns	$V_{DD} \cong 10V$
Turn-off delay time	$\mathbf{t}_{d(off)}$	_	200	_	ns	
Fall time	t _f	_	230	_	ns	
Body to drain diode forward voltage	V_{DF}		0.9	_	V	$I_F = 15A, V_{GS} = 0^{*1}$
Body to drain diode reverse recovery time	t _{rr}	_	55		ns	$I_F = 15A, V_{GS} = 0$ diF/ dt = 20A/µs

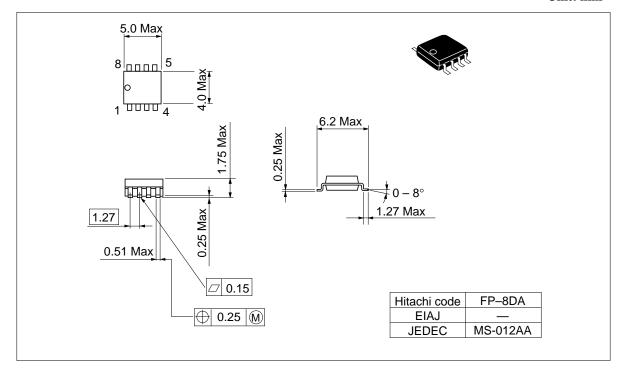
Note: 1. Pulse test

Main Characteristics



Package Dimensions

Unit: mm



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